



SiC SCHOTTKY DIODE TYPE 3A

Features

- High surge current capable
- Zero reverse recovery current
- High bandwidth
- RoHS compliant
- Temperature Independent Switching Behavior
- High temperature soldering guaranteed: 260°C / 10 seconds at terminals
- VDC 650 V
- I_F (T_C<150°C) 3 A

Benefits

- Unipolar rectifier
- Zero switching loss
- Higher efficiency
- Smaller heat sink
- Parallel devices without thermal runaway

Applications

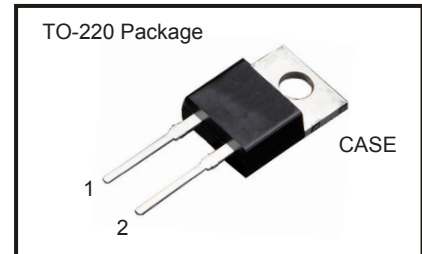
- Motor drives
- Switch mode power supplies
- Ev chargers
- Solar inverters
- Welding equipment
- Power factor correction
- Diode snubber
- Automotive
- induction heating

Maximum Ratings

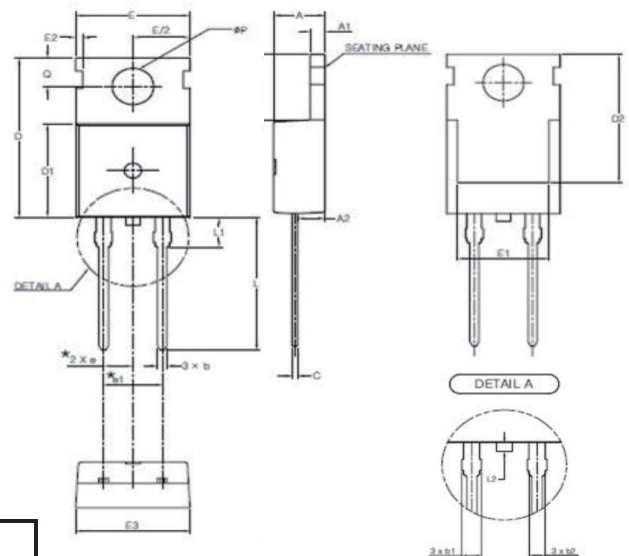
Operating Junction Temperature : -55°C to +175°C
 Storage Temperature : -55°C to +175°C

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum DC Blocking Voltage
CSR03065	650V	650V

Maximum Rating	Symbol	Conditions	Value	Unit
Continuous forward current	I _F	T _C =150 °C	3	A
Surge non-repetitive forward current sine halfwave	I _{FSM}	T _C =25 °C, t _p =8.3 ms	24	
		T _C =150 °C, t _p =8.3 ms	15	
Non-repetitive peak forward current	I _{F,max}	T _C =25 °C, t _p =10 μs	60	
Repetitive peak reverse voltage	V _{RRM}	T _j =25 °C	650	V

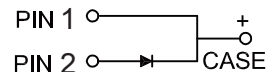


Package Dimensions



SYMBOL	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	1.25	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	0.90
b1	1.42	1.52	1.62
b2	1.17	1.27	1.37
c	0.45	0.50	0.60
D	15.50	15.70	15.90
D1	9.00	9.20	9.40
D2	(12.70)		
E	9.00	9.20	9.40
E1	(8.00)		
E2	(0.60)		
E3	9.70	9.90	10.10
e	2.54 BSC		
e1	5.08 BSC		
H1	6.30	6.50	6.70
L	12.88	13.08	13.28
L1	(3.00)		
L2	-	-	0.80
φP	3.50	3.60	3.70
Q	2.70	2.80	2.90

NOTE
 1. THESE DIMENSIONS DO NOT INCLUDE PROTRUSIONS OF THE MOLD.
 2. THE '()' MARK IS THE REFERENCE
 3. THE 'L2' SYMBOL IS A PROTRUSION OF THE MOLD.





Electrical Characteristics, at T_j=25 °C, unless otherwise specified.

Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
DC blocking voltage	V _{DC}		650	-	-	V
Diode forward voltage	V _F	I _F =3A, T _j =25 °C	-	1.45	1.65	
		I _F =3A, T _j =175 °C	-	1.65	2.20	
Reverse current	I _R	V _R =650V, T _j =25 °C	-	3	30	μA
		V _R =650V, T _j =175 °C	-	50	300	

AC Characteristics

Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Total capacitive charge	Q _c	V _R =650V, T _j =25 °C	-	7	-	nC
Total capacitance	C	V _R =1V, f=1 MHz T _j =25 °C	-	158	-	pF
		V _R =325V, f=1 MHz T _j =25 °C	-	13	-	
		V _R =650V, f=1 MHz T _j =25 °C	-	11	-	

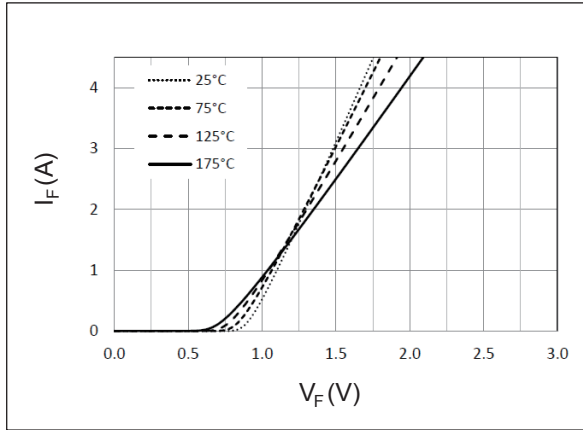
Thermal Characteristics

Static Characteristics	Symbol	Values	Unit
		typ.	
Thermal resistance from junction to case	R _{θJC}	4.18	°C/W

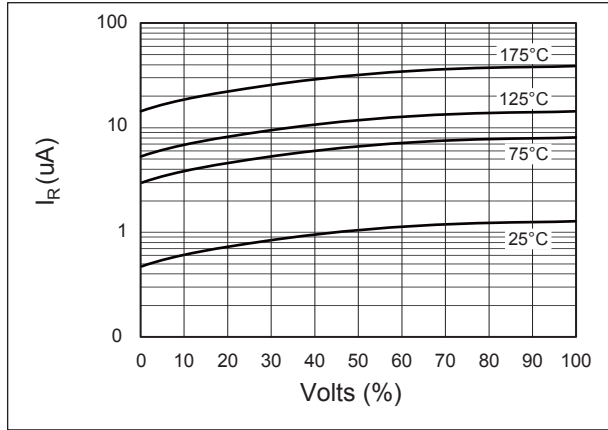


Typical Performance

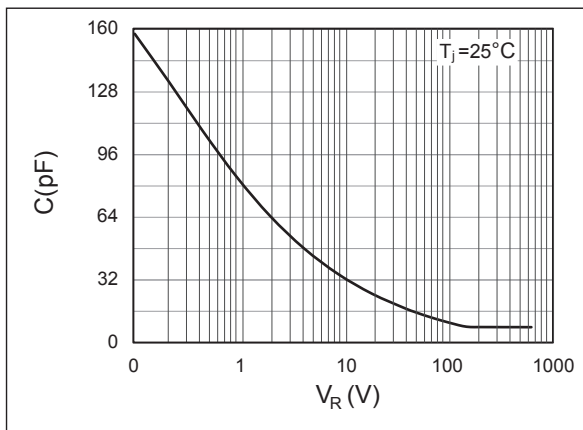
Forward Characteristics (parameterized on T_j)



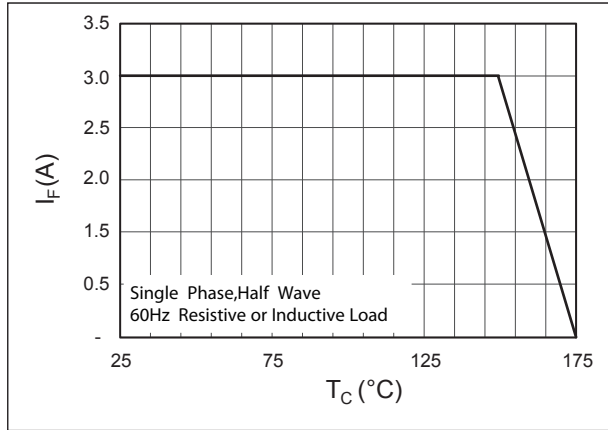
Reverse Characteristics (parameterized on T_j)



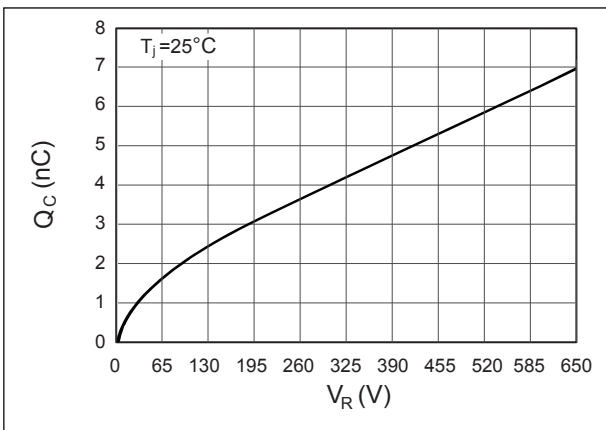
Capacitance



Current Derating



Recovery Charge



Forward Surge Current

